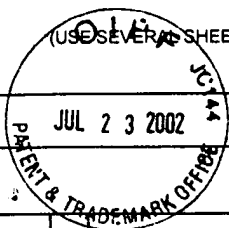


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. IMEC239.001AUS	APPLICATION NO. 10/091,226
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Vandervorst, et al.	
		FILING DATE February 28, 2002	GROUP 2812



U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
RR	5,585,734	12/17/1996	Meuris, et al.	—	—	
RR	6,091,248	07/18/2000	Hellemans, et al.	—	—	
RR	5,412,980	05/09/1995	Elings, et al.	—	—	

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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
RR	Olbrich, et al., <i>Nanoscale Electrical Characterization of Thin Oxides with Conducting Atomic Force Microscopy</i> , 1998, proceedings of the 36 th Annual International Reliability Physics Symposium, Reno, Nevada, Pages 163-168
RR	H. Edwards, et al., <i>pn-junction delineation in Si devices using scanning capacitance spectroscopy</i> , February 1, 2000, Journal of Applied Physics, vol. 87, no. 3.

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EXAMINER	RAEVIS	DATE CONSIDERED	8-26-03
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